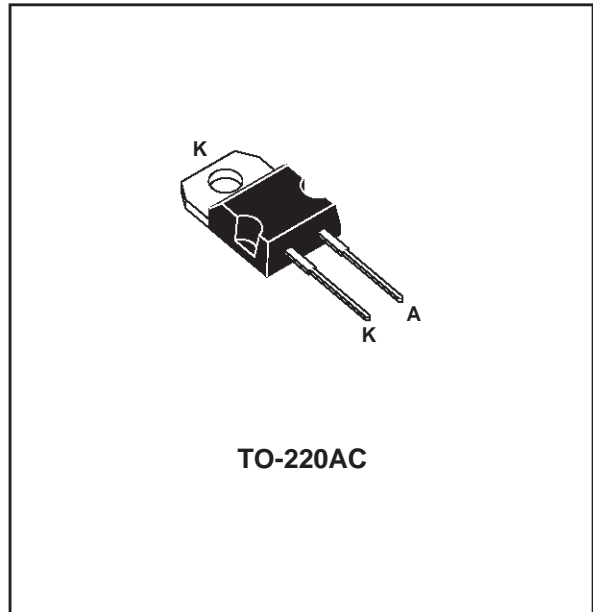


TURBOSWITCH™ ULTRA-FAST HIGH VOLTAGE DIODE
MAIN PRODUCT CHARACTERISTICS

$I_{F(AV)}$	12A
V_{RRM}	1200V
$t_{rr}(typ)$	50 ns
$V_F(max)$	2.0 V

FEATURES AND BENEFITS

- ULTRA-FAST, SOFT RECOVERY.
- VERY LOW OVERALL POWER LOSSES IN BOTH THE DIODE AND THE COMPANION TRANSISTOR.
- HIGH FREQUENCY AND/OR HIGH PULSED CURRENT OPERATION.
- HIGH REVERSE VOLTAGE CAPABILITY.


DESCRIPTION

TURBOSWITCH 1200V drastically cuts losses in all high voltage operations which require extremely fast, soft and noise-free power diodes. Due to their optimized switching performances they also highly decrease power losses in any associated switching IGBT or MOSFET in all freewheel mode operations.

They are particularly suitable in motor control circuitries, or in the primary of SMPS as snubber, clamping or demagnetizing diodes. They are also suitable for secondary of SMPS as high voltage rectifier diodes.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage		1200	V
$I_{F(RMS)}$	RMS forward current		30	A
I_{FRM}	Repetitive peak forward current	$t_p = 5 \mu s$ $F = 5 kHz$ square	160	A
I_{FSM}	Surge non repetitive forward current	$t_p = 10ms$ sinusoidal	100	A
T_{stg}	Storage temperature range		- 65 to + 150	°C
T_j	Maximum operating junction temperature		150	°C

THERMAL AND POWER DATA

Symbol	Parameter	Test conditions	Value	Unit
$R_{th(j-c)}$	Junction to case thermal resistance		1.9	°C/W
P_1	Conduction power dissipation	$I_{F(AV)} = 12A$ $\delta = 0.5$ $T_C = 95^\circ C$	29.2	W
P_{max}	Total power dissipation $P_{max} = P_1 + P_3$ ($P_3 = 10\% P_1$)	$T_C = 89^\circ C$	32.1	W

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test conditions		Min	Typ	Max	Unit
V_F^*	Forward voltage drop	$I_F = 12A$	$T_j = 25^\circ C$ $T_j = 125^\circ C$		1.35	2.2 2.0	V V
I_R^{**}	Reverse leakage current	$V_R = 0.8 \times V_{RRM}$	$T_j = 25^\circ C$ $T_j = 125^\circ C$		0.8	100 5.0	μA mA
V_{to}	Threshold voltage	$I_p < 3 \cdot I_{F(AV)}$	$T_j = 125^\circ C$			1.57	V
R_d	Dynamic resistance					36	m Ω

Test pulses : * $t_p = 380 \mu s$, $\delta < 2\%$
 ** $t_p = 5 ms$, $\delta < 2\%$

To evaluate the maximum conduction losses use the following equation :

$$P = V_{to} \times I_{F(AV)} + R_d \times I_F^2(RMS)$$

DYNAMIC ELECTRICAL CHARACTERISTICS

TURN-OFF SWITCHING

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
t_{rr}	Reverse recovery time	$T_j = 25^\circ C$ $I_F = 0.5 A$ $I_R = 1A$ $I_{rr} = 0.25A$ $I_F = 1 A$ $di_F/dt = -50A/\mu s$ $V_R = 30V$		50	100	ns
I_{RM}	Maximum reverse recovery current	$T_j = 125^\circ C$ $V_R = 600V$ $I_F = 12A$ $di_F/dt = -96 A/\mu s$ $di_F/dt = -500 A/\mu s$		30	18	A
S_{factor}	Softness factor	$T_j = 125^\circ C$ $V_R = 600V$ $I_F = 12A$ $di_F/dt = -500 A/\mu s$		1.2		/

TURN-ON SWITCHING

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
t_{fr}	Forward recovery time	$T_j = 25^\circ C$ $I_F = 12A$, $di_F/dt = 96 A/\mu s$ measured at $1.1 \times V_{Fmax}$			900	ns
V_{FP}	Peak forward voltage	$T_j = 25^\circ C$ $I_F = 12A$, $di_F/dt = 96 A/\mu s$ $I_F = 40A$, $di_F/dt = 500 A/\mu s$		40	30	V

Fig. 1: Conduction losses versus average current.

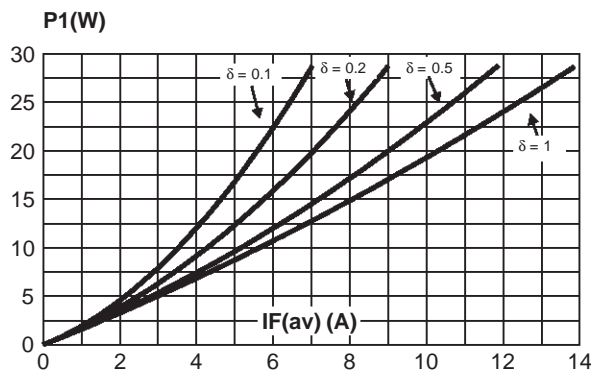


Fig. 2: Forward voltage drop versus forward current (maximum values).

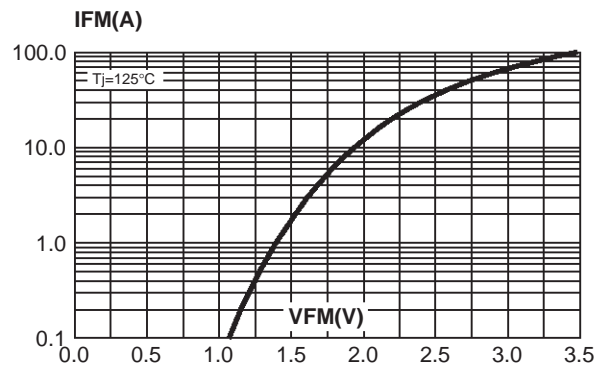


Fig. 3: Relative variation of thermal impedance junction to case versus pulse duration.

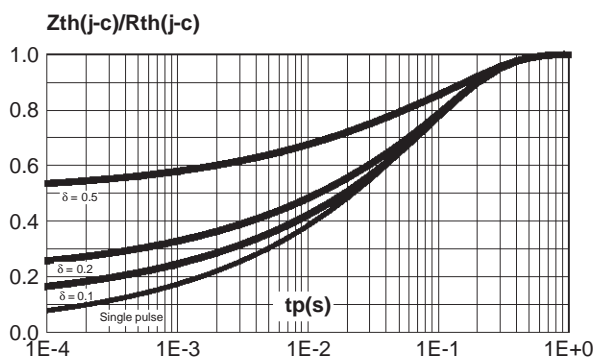


Fig. 4: Peak reverse recovery current versus dI_F/dt (90% confidence).

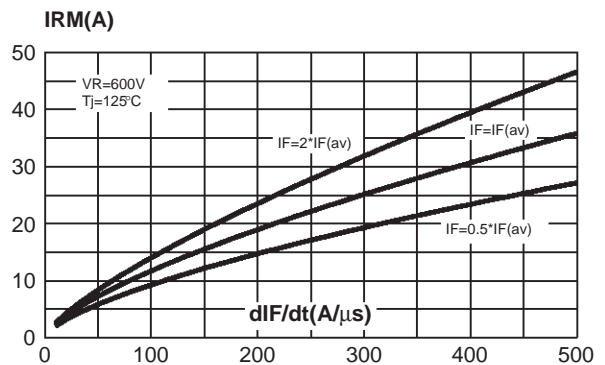


Fig. 5: Reverse recovery time versus dI_F/dt (90% confidence).

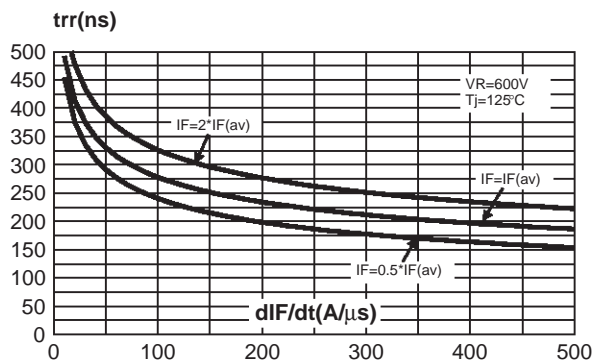


Fig. 6: Softness factor (tb/ta) versus dI_F/dt (typical values).

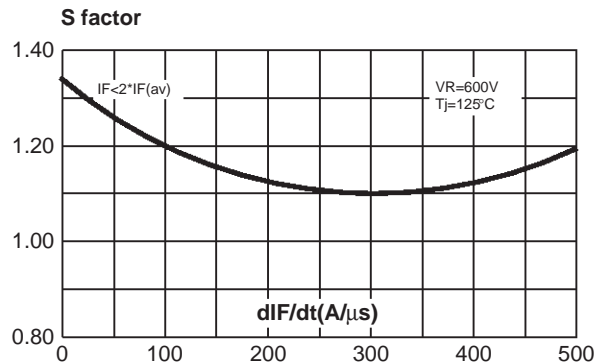


Fig. 7: Relative variation of dynamic parameters versus junction temperature (reference $T_j=125^\circ\text{C}$).

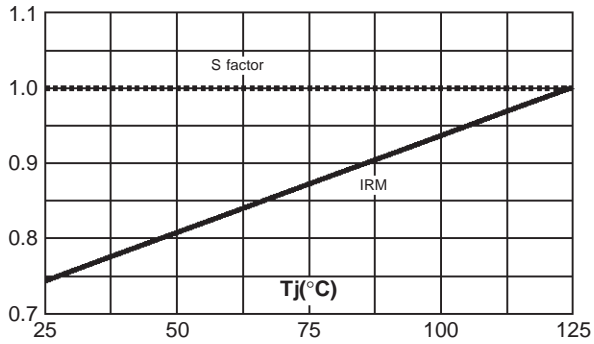


Fig. 8: Transient peak forward voltage versus dI_F/dt (90% confidence).

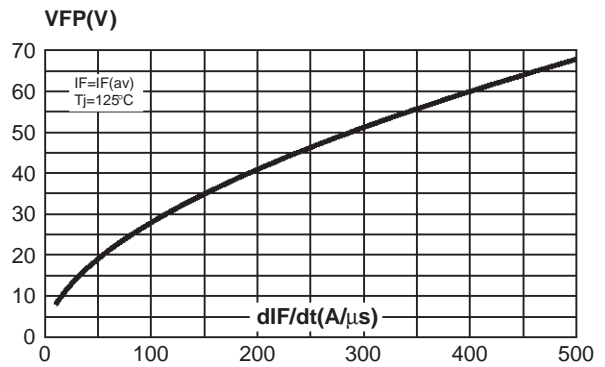
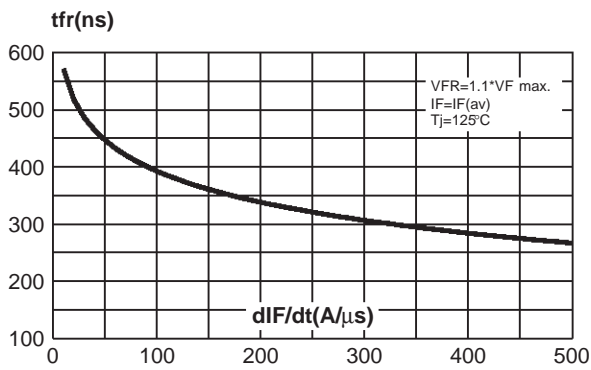


Fig. 9: Forward recovery time versus dI_F/dt (90% confidence).



APPLICATION DATA

The 1200V TURBOSWITCH series has been designed to provide the lowest overall power losses in all high frequency or high pulsed current operations. In such applications (Fig A to D), the way of calculating the power losses is given below :

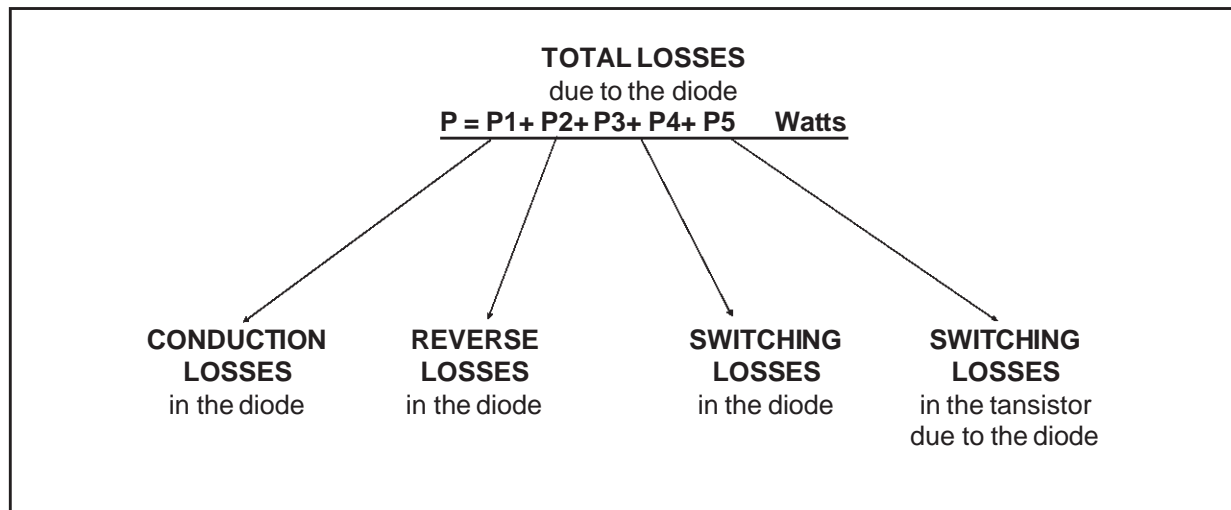


Fig. A : "FREEWHEEL" MODE.

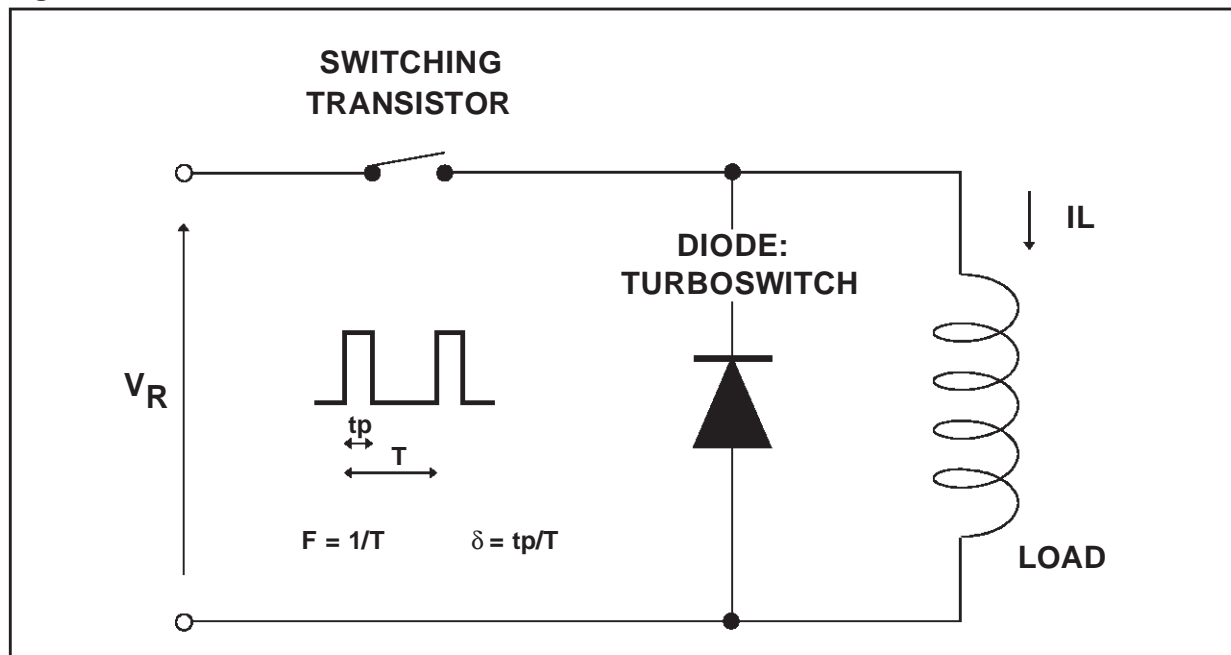


Fig. B : SNUBBER DIODE.

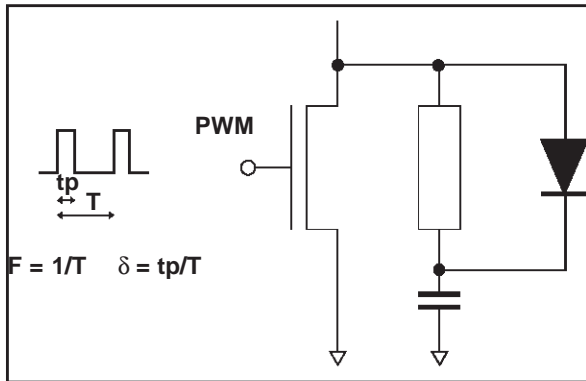


Fig. C : DEMAGNETIZING DIODE.

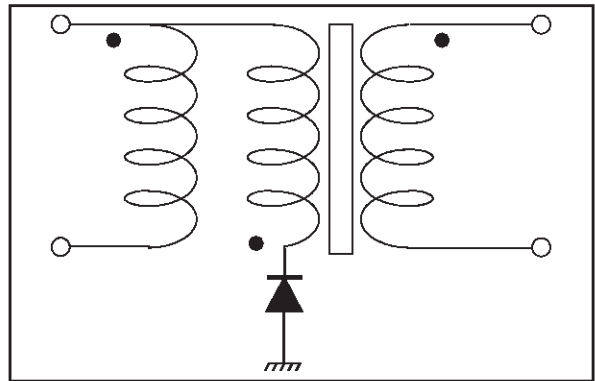
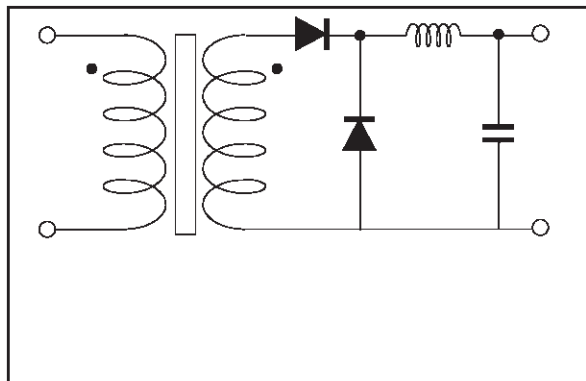
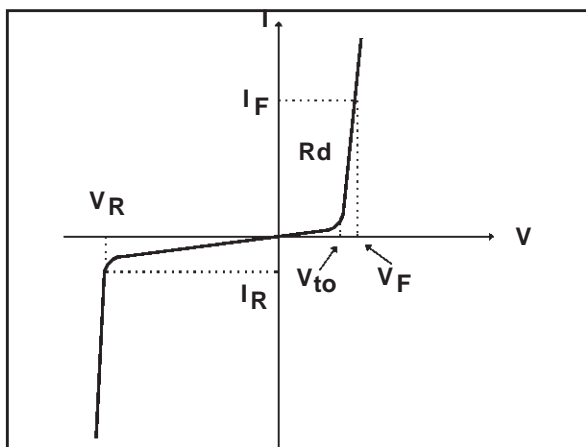


Fig. D : RECTIFIER DIODE.



STATIC & DYNAMIC CHARACTERISTICS . POWER LOSSES .

Fig. E: STATIC CHARACTERISTICS



Conduction losses :

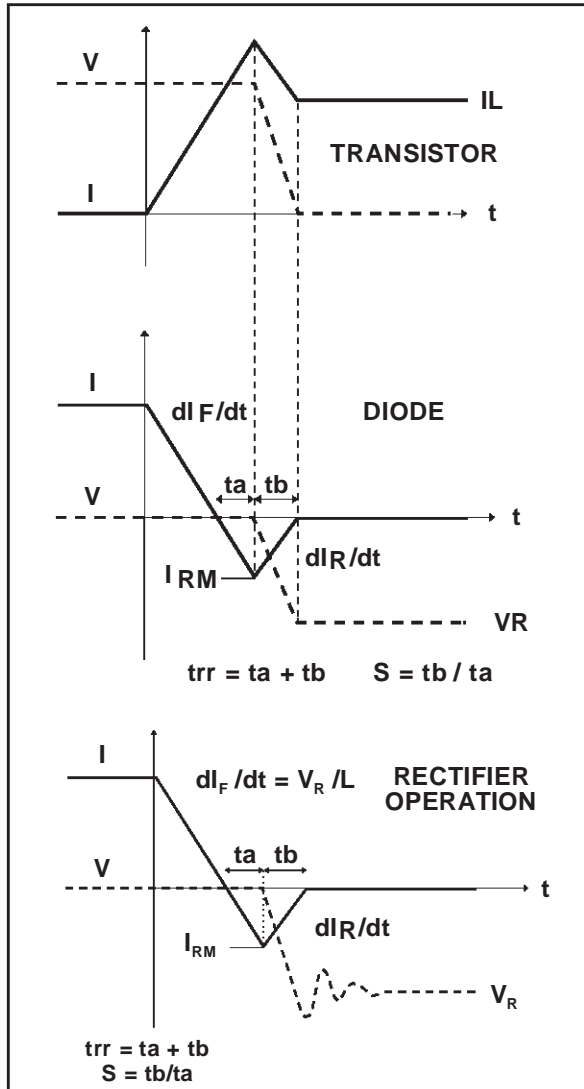
$$P1 = V_{to} \cdot I_F(AV) + R_d \cdot I_F^2(RMS)$$

Reverse losses :

$$P2 = V_R \cdot I_R \cdot (1 - \delta)$$

APPLICATION DATA (Cont'd)

Fig. F: TURN-OFF CHARACTERISTICS



Turn-on losses:
(in the transistor, due to the diode)

$$P5 = \frac{V_R \times I_{RM}^2 \times (3 + 2 \times S) \times F}{6 \times dI_F/dt} + \frac{V_R \times I_{RM} \times I_L \times (S + 2) \times F}{2 \times dI_F/dt}$$

Turn-off losses (in the diode):

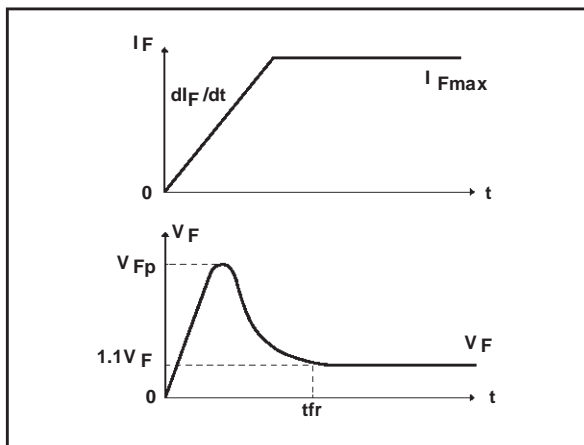
$$P3 = \frac{V_R \times I_{RM}^2 \times S \times F}{6 \times dI_F/dt}$$

Turn-off losses:
(with non negligible serial inductance)

$$P3' = \frac{V_R \times I_{RM}^2 \times S \times F}{6 \times dI_F/dt} + \frac{L \times I_{RM}^2 \times F}{2}$$

P3, P3' and P5 are suitable for power MOSFET and IGBT

Fig. G: TURN-ON CHARACTERISTICS



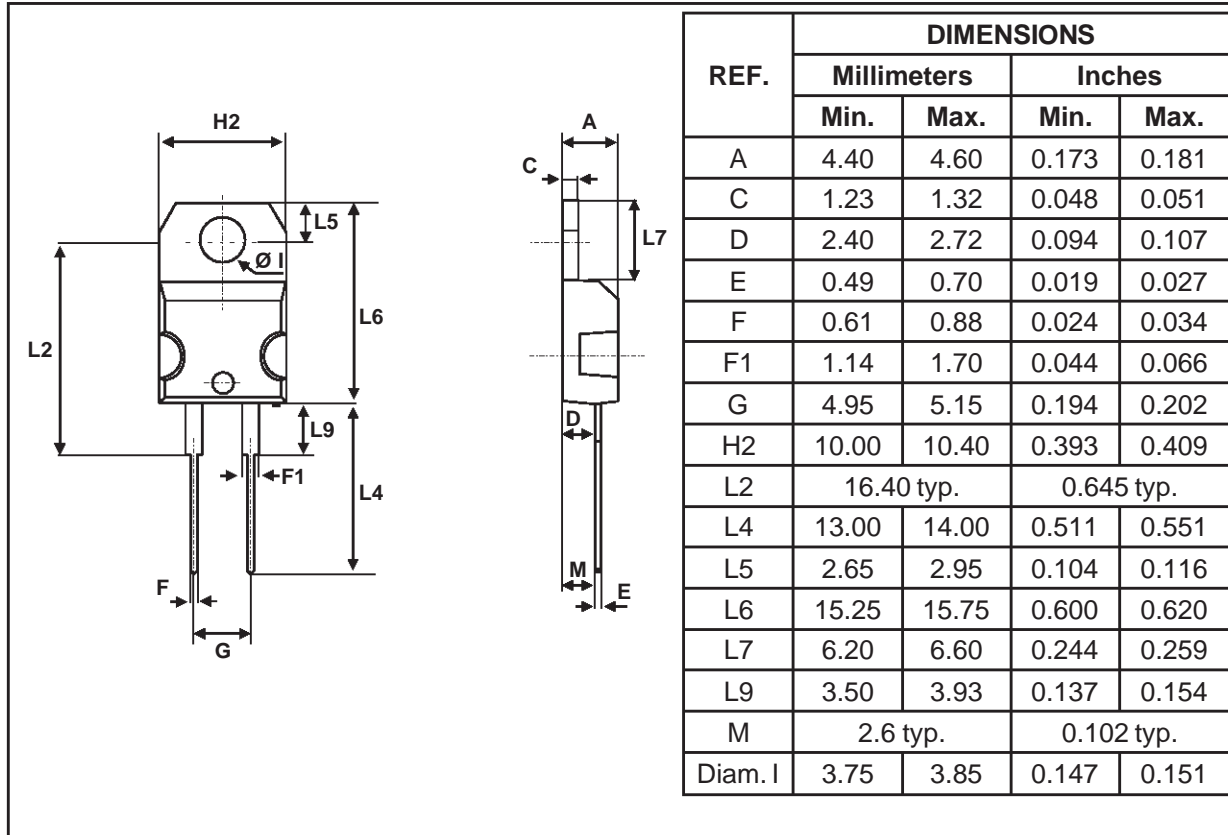
Turn-on losses:

$$P4 = 0.4 (V_{FP} - V_F) \cdot I_{Fmax} \cdot t_{fr} \cdot F$$

STTA1212D

PACKAGE DATA

TO-220AC (JEDEC outline)



Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STTA1212D	STTA1212D	TO-220AC	1.86g	50	Tube

- Cooling method: by conduction (C)
- Recommended torque value: 0.55 N.m.
- Maximum torque value: 0.70 N.m.
- Epoxy meets UL94,V0

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